International TOR Rectifier

HFA15TB60

HEXERED™

Ultrafast, Soft Recovery Diode

Features

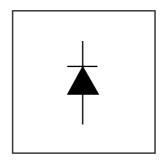
- · Ultrafast Recovery
- · Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Guaranteed Avalanche
- · Specified at Operating Conditions

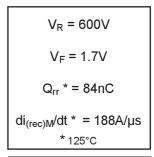
Benefits

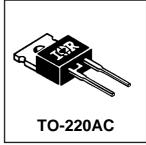
- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- · Reduced Snubbing
- · Reduced Parts Count

Description

International Rectifier's HFA15TB60 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA15TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA15TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.







Absolute Maximum Ratings

	Parameter	Max.	Units
V _R	Cathode-to-Anode Voltage	600	V
I _F @ T _C = 25°C	Continuous Forward Current		
I _F @ T _C = 100°C	Continuous Forward Current	15	Α
I _{FSM}	Single Pulse Forward Current	150] '`
I _{FRM}	Maximum Repetitive Forward Current	60	
E _{AS} ①	Maximum Single Pulse Avalanche Energy	28	mJ
I _{AR} ②	Maximum Repetitive Avalanche Current	15	Α
P _D @ T _C = 25°C	Maximum Power Dissipation	74	W
P _D @ T _C = 100°C	Maximum Power Dissipation	29	7 "
TJ	Operating Junction and	-55 to +150	С
T _{STG}	Storage Temperature Range	-55 to +150	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions	
V_{BR}	Cathode Anode Breakdown Voltage	600			V	I _R = 100μA	
V _{FM}	Max Forward Voltage		1.3	1.7	>	I _F = 15A	
			1.5	2.0		I _F = 30A See Fig. 1	
			1.2	1.6		I _F = 15A, T _J = 125°C	
I _{RM}	Max Reverse Leakage Current		1.0	10	μA	$V_R = V_R$ Rated See Fig. 2	
			400	1000		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ Rated	
Ст	Junction Capacitance		25	50	pF	V _R = 200V See Fig. 3	
L _S	Series Inductance		8.0		nH	Measured lead to lead 5mm from	
						package body	

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t _{rr}	Reverse Recovery Time		19			$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30$		
t _{rr1}	See Fig. 5, 6 & 16		42	60	ns	T _J = 25°C		
t _{rr2}]		74	120		T _J = 125°C	I _F = 15A	
I _{RRM1}	Peak Recovery Current		4.0	6.0	Α	T _J = 25°C		
I _{RRM2}	See Fig. 7& 8		6.5	10	Α .	T _J = 125°C	V _R = 200V	
Q _{rr1}	Reverse Recovery Charge		84	180	nC	T _J = 25°C		
Q _{rr2}	See Fig. 9 & 10		241	600	IIC	T _J = 125°C	$di_f/dt = 200A/\mu s$	
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		188		A/us	T _J = 25°C		
di _{(rec)M} /dt2	During t _b See Fig. 11 & 12		160		Α/µS	T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameter	Min.	Тур.	Max.	Units			
T _{lead} ③	Lead Temperature			300	°C			
$R_{\theta JC}$	Thermal Resistance, Junction to Case			1.7				
R _{0JA} @	Thermal Resistance, Junction to Ambient			80	K/W			
R _{θCS} ⑤	Thermal Resistance, Case to Heat Sink		0.5		1			
VVt	Weight		2.0		g			
	vveigni		0.07		(oz)			
Т	Mounting Torque	6.0		12	Kg-cm			
	Wodning Forque	5.0		10	lbf•in			

- $\begin{array}{ll} \textcircled{1} & \text{I_L = 15A, L = 250μH, T_C = 100°C$} \\ \textcircled{2} & \text{L = 100μH, duty cycle limited by max T_J} \end{array}$
- ③ 0.063 in. from Case (1.6mm) for 10 sec
- Typical Socket Mount
- Mounting Surface, Flat, Smooth and Greased

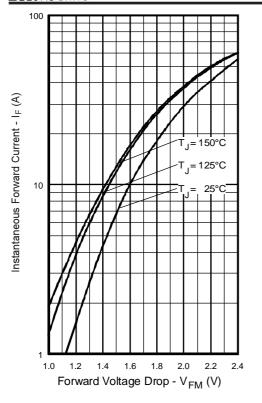


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

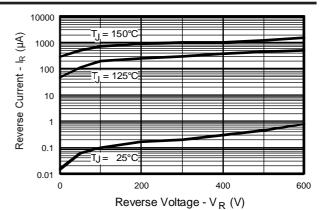


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

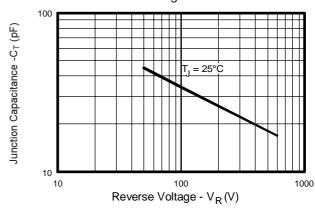


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

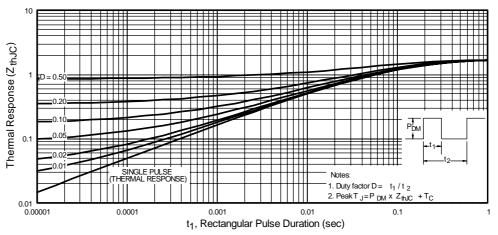


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

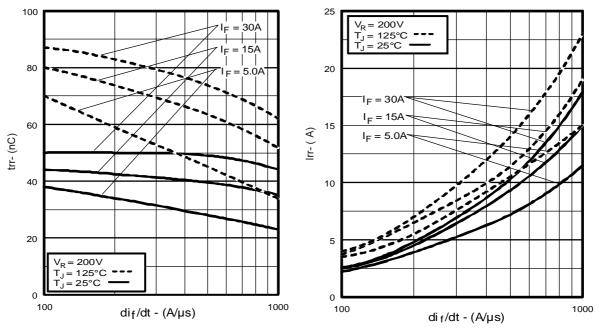


Fig. 5 - Typical Reverse Recovery vs. di_f/dt



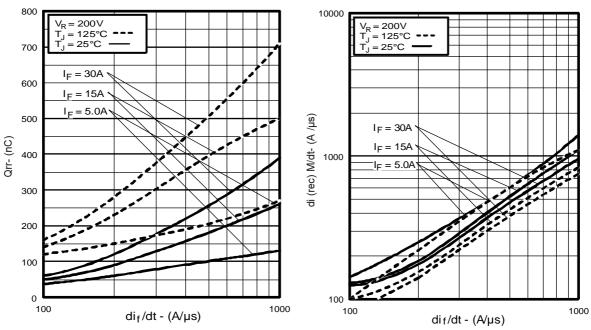


Fig. 7 - Typical Stored Charge vs. di_f/dt

Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

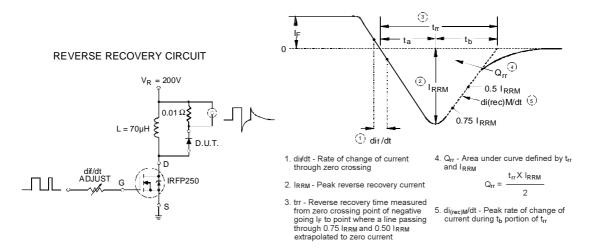


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

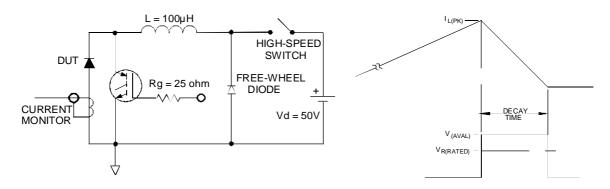
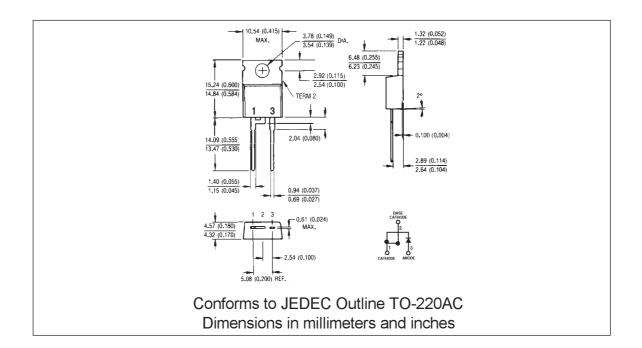


Fig. 11 - Avalanche Test Circuit and Waveforms



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